

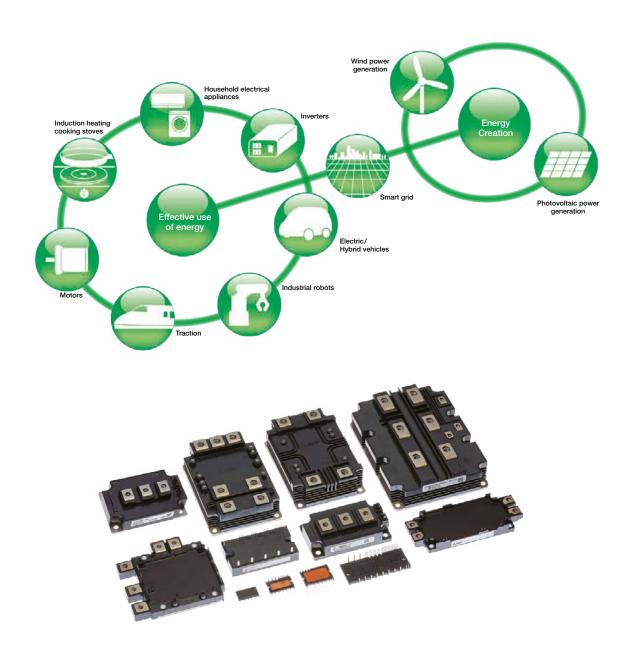
**POWER DEVICES** 

### POWER DEVICES



# Innovative Power Devices for a Sustainable Future

Mitsubishi Electric power modules are at the forefront of the latest energy innovations that seek to solve global environmental issues while creating a more affluent and comfortable society for all. Some of these innovations are photovoltaic (PV) and wind power generation from renewable energy sources, smart grids realizing efficient supply of power, hybrid/electric vehicles (HVs/EVs) that take the next step in reducing carbon emissions and fuel consumption, and home appliances that achieve ground-breaking energy savings. Whether in appliances, railcars, EVs or industrial systems, our power modules are key elements in changing the way energy is used.



### Index

			Conne	ection		Poted	Datad		
Product	Page	IGBT Module	Intelligent Power Module	MOSFET Module	Diode Module	Rated voltage	Rated current	Main Application	
						600V	15A-30A		
SiC	5-12	,	,	,	,	1200V	75A-1200A		
Power Modules	5-12	(Hybrid)				1700V	300A-1200A	Home Appliance Industrial equipment	
		-				3300V	185A-800A	Traction	
SOPIPM	13		<b>✓</b>			600V	2A	Home Appliance	
DIPIPM	13-18		./			600V	5A-75A		
DII II W	10 10					1200V	5A-100A	Home Appliance	
						600V	75A		
IPM	19-22		<b>✓</b>			650V	50A-450A		
						1200V	25A-450A	Industrial equipment	
						600V	200A-600A		
						650V	50A-600A		
IGBT Modules	23-32	<b>✓</b>				1200V	35A-1400A		
Wodules						1700V	75A-1200A	Industrial equipment	
						2000V	200A-1200A		
						1700V	600A-2400A		
HVIGBT	22.20	,				3300V	400A-1800A		
Modules	33-36	<b>V</b>				4500V	450A-1500A	Traction High Power	
						6500V	600A-1000A	Traction riight ower	
						3300V	600A-1200A		
HVDIODE Modules	37-38				<b>✓</b>	4500V	450A-1500A		
Modulos						6500V	300A-1000A	Traction High Power	
						75V			
MOSFET Modules	39	39		<b>/</b>		100V	100A-300A		
MICGUICO						150V		Industrial equipment	
Power Modules for xEV*1	40-41	<b>✓</b>				650V	600A-700A	xEV	

<sup>\*1</sup> EV: Electric Vehicle

 $<sup>^{*}</sup>$ 2 SOPIPM, DIPIPM, SLIMDIP, DIPIPM+, DIPPFC and CSTBT are trademarks of Mitsubishi Electric

# Development of Mitsubishi Electric SiC Power Devices and Power Electronics Equipment Incorporating Them

Mitsubishi Electric began developing SiC as a new material in the early 1990s. Pursuing special characteristics, we succeeded in developing various elemental technologies.

In 2010, we commercialized the first air conditioner in the world equipped with a SiC power device.

Furthermore, substantial energy-saving effects have been achieved for traction and FA machinery.

We will continue to provide competitive SiC power modules with advanced development and achievements from now on.



January 2010 Developed large-capacity power module equipped with SiC diode October 2010 Launched "Kirigamine" inverter air conditioner





### 2011

January 2011 Verified highest power conversion efficiency\*1 for solar power generation system power conditioner (domestic industry)\*2

October 2011 Commercialized SiC inverter for use in railcars



### 2014

February 2014 Developed EV motor drive system with built-in SiC inverter



# May 2014 Began shipping samples of hybrid SiC power modules for high-frequency switching applications



November 2014 Launched Large Hybrid SiC DIPIPM™ for PV Applications



### <sub>Early</sub> 1990s

Developed new material, silicon-carbide (SiC) power semiconductor, maintaining a lead over other companies

### 2000s

Developed various elemental technologies

### 2006

January 2006 Successfully developed SiC inverter for driving motor rated at 3.7kW

### 2009

February 2009 Verified 11kW SiC inverter, world's highest value\*1 with approx. 70% reduction in power loss



November 2009 Verified 20kW SiC inverter, world's highest value\*1 with approx. 90% reduction in power loss



### 2012

March 2012 Developed motor system with built-in SiC inverter



September 2012 Verified built-in main circuit system for railcars



# July 2012 Began shipping samples of hybrid SiC power modules



December 2012 Launched CNC drive unit equipped with SiC power module



### 2013

February 2013 Developed SiC for application in elevator control systems

March 2013
Delivered auxiliary power supply systems for railcars



### Contributing to the realization of a low-carbon society and more affluent lifestyles

### 2017

#### March 2017 Launched SiC-SBD



March 2017 Develops World's smallest SiC Inverter for HEVs.



December 2017 Mitsubishi Electric and the University of Tokyo Quantify Factors for Reducing SiC Power Semiconductor Resistance by Two-Thirds

### 2018

January 2018 New 6.5kV Full-SiC Power Semiconductor Module Achieves World's Highest Power Density

December 2018 Mitsubishi Electric and the University of Tokyo Reveal New Mechanism for Enhancing Reliability of SiC Power Semiconductor Devices

March 2024 J3-Series Full-SiC **Power Mdules** Began shipping samples



January 2021 Launched Second-generation **Full-SiC Power Modules** 



### 2020

November 2020 Launched 4-terminal SiC-MOSFETs





July 2020 **Develops Accurate Circuit** Simulation Technology for SiC-MOSFETs

### 2015

January 2015 Launched power conditioner for PV equipped with full SiC-IPM\*2

June 2015

Railcar traction system with full SiC power modules installed in Shinkansen bullet trains

### 2019

June 2019 **Began shipping** samples of 1200V SiC-SBD

February 2019 **Develops Super Compact Power** Unit for Hybrid Electric Vehicle

September 2019 Trench-type SiC-MOSFET with unique electric-field-limiting structure developed

October 2016



February 2013 Developed technologies to increase capacities of SiC power modules



May 2013 Launched SiC power modules



December 2013 Launched railcar traction inverter with full SiC power module



### 2016

**April 2016** Launched Super mini **Full SiC DIPIPM** 

> May 2016 Launched room air conditioners with full SiC DIPIPM in Japan



Launched package air conditioners with full SiC DIPIPM in Japan







<sup>\*</sup> The year and month listed are based on press releases or information released during the product launch month in Japan.

<sup>\*1</sup> Researched in press releases by Mitsubishi Electric. \*2 Mitsubishi Electric solar-power generation system discontinued on March 31, 2020.

### **SiC Power Modules**

Data sheet here



### ■Lineup of SiC Power Modules

Application	Product name	Model	Rat Voltages[V]	ting Current[A]	Connection	States	Page
		FMF300BXZ-24B	1 1011	300			7
		FMF400BX-24B	-	400	4 in 1		6
		FMF400BXZ-24B		400			7
		RMF400DU-24B	-	400	2 in1(Diode)		
		FMF400DY-24B	_	400			6
		FMF600DXZA-24B	1200	600			7
	Full SiC Power Modules	FMF600DXE-24BN	_	600			
		FMF800DX-24B	_	800	2 in 1		6
		FMF800DXZA-24B	_	800			
		FMF1200DXZ-24B	_	1200	-		
Industrial		FMF300DXZ-34B		300			7
equipment		FMF300E3XZ-34B	1700	300	2 in 1 (Chopper)		
		FMF600DXE-34BN		600	2 in 1	_	6
		PMF75CGA120		000			
	Full SiC-IPM	PMF75CGAL120	1200	75	6 in 1		7
	Hybrid SiC Power Modules for High-frequency Switching Applications	CMH100DY-24NFH		100	2in1	Commercially	
		CMH150DY-24NFH	-	150		available	
		CMH200DU-24NFH	-	200			
		CMH300DU-24NFH	1200	300			
		CMH400DU-24NFH	-	400			
		CMH600DU-24NFH	-	600			
		CMH400HC6-24NFM	-	400	1in1		8
		FMF185DC-66A		185			
		FMF375DC-66A	-	375	-		
	Full SiC Power Modules	FMF750DC-66A	3300	750			
raction inverter		FMF750DC-66A-1	-	750	2in1		
HVDC system		FMF800DC-66BEW	-	800			
		CMH600DC-66X	3300	600			
	Hybrid SiC Power Modules	CMH1200DC-34S	1700	1700 1200			
		PSF15S92F6-A6		15			9
Home appliances	Ful SiC Super mini DIPIPM	PSF25S92F6-A6	600	25	6 in 1		
	Ful SiC Super mini DIPPFC	PSF30L92A6-A	600	30	2 Phase interleaved PFC		10

6

**New Products** 

## NX-type Full-SiC Power Modules for Industrial Equipment FMF600DXE-24BN/FMF600DXE-34BN Commercially available

Will contribute to more efficient, smaller and lighter industrial equipment by reducing internal inductance and incorporating an SiC chip

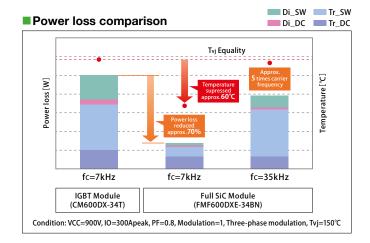
#### ■ Features

- Electrode structure optimized to achieve internal inductance of 9nH, 47% lower than that of the existing module\*
- NX-type package compatibility allows new module to easily replace current version
- Power loss reduced approx. 70% compared to the conventional product\*
- \* Comparison with the same rated value of the conventional 7th Gen. IGBT modules

#### ■ Product lineup

Model	Rated voltage	Rated current	Circuit configuration	Package size (D x W)
FMF600DXE-24BN 1200V		600A	2 in 1	62×152mm
FMF600DXE-34BN	1700V	OUUA	Z III I	UZXIOZIIIII







### **Full-SiC Power Modules for Industrial Equipment**

Commercially available

### Contributes to reducing size/weight of industrial-use inverters

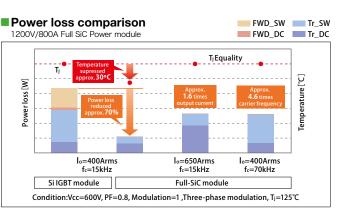
#### ■ Features

- Power loss reduced approx. 70% compared to the conventional product\*
- Low-inductance package(92.3mm x 121.7mm) adopted to deliver full SiC performance
- Package compatible with the conventional product(62mm x 108mm, 28mm terminal pitch)
- Contributes to incereasing the output current and downsizing peripheral components by low power loss characteristics of SiC
- \* Comparison with the same rated value of the conventional 7th Gen. IGBT modules

#### ■ Product lineup

Model	Rated voltage	Rated current	Circuit configuration	Package size (D x W)
FMF400BX-24B			4 in 1	92.3×121.7mm
RMF400DU-24B	1200V	400A	2in1(Diode)	80×110mm
FMF400DY-24B	12000		0: 1	62×108mm
FMF800DX-24B		800A	2 in 1	92.3×121.7mm







### **Full-SiC Power Modules for Industrial Equipment** (built-in short-circuit protection function) Commercially available

### Contributes to enhancing the performance of industrial-use inverters thanks to built-in protection function for short circuit

#### ■ Features

- · By using short circuit monitoring circuit in the module it is possible to transfer a short circuit detection signal to the system side
- Power loss reduced approx.80% compared to the conventional product\*
- · Low- inductance package adopted to deliver full SiC performance
- \*Comparison with the same rated value of the conventional 7th Gen. IGBT modules

#### ■ Product lineup

Model	Rated voltage	Rated current	Circuit configuration	Package size (D x W)	
FMF300BXZ-24B		300A	4 in 1		
FMF400BXZ-24B		400A	4 in 1	79.6x122mm	
FMF600DXZA-24B*	1200V	600A	2 in 1	79.0x12211111	
FMF800DXZA-24B*		800A	2 in 1		
FMF1200DXZ-24B		1200A	2 in 1	152×122mm	
FMF300DXZ-34B	1700V	300A	2 in 1	79.6x122mm	
FMF300E3XZ-34B	17000	300A	2 in 1 (Chopper)	79.0×122mm	
	•	•	•	★:New Product	

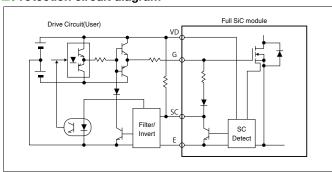


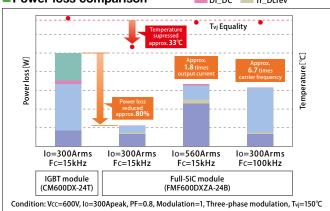
Power loss comparison

Di SW Tr SW Di\_DC Tr\_Dcrev

Tr DC

### ■ Protection circuit diagram





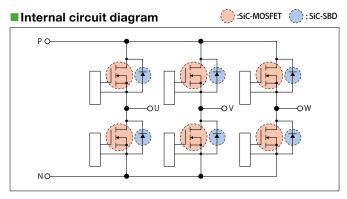


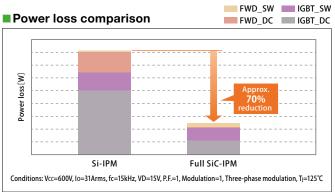
### 1200V/75A Full SiC-IPM for Industrial Equipment PMF75CGA120/PMF75CGAL120 Commercially available

SiC chips(MOSFET and Schottky Barrier Diode) incorporated in an IPM with a built-in drive circuit and protection functions Power loss reduction of approx.70% contributes to improving the performance of industrial equipment

- · Realized high performance and low power loss by 2nd. generation SiC-MOSFET and SiC-SBD with current sense and temperature sense
- External size is reduced approx.30% with the conventional Silicon IPM products\* of the same rating.
- · Available to drive it by the equivalent I/F and power supply circuit with the Silicon IPM products.

\* Conventional product: Mitsubishi Electric G1 Series PM75CG1B120







### **Hybrid SiC Power Modules for High-frequency** Switching Applications Commercially available

### For optimal operation of power electronics devices that conduct high-frequency switching

#### ■ Features

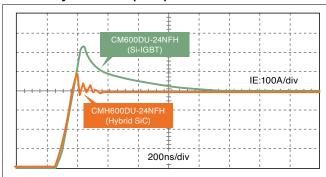
- Power loss reduction of approx. 40% contributes to higher efficiency, smaller size and weight reduction of total system
- Suppresses surge voltage by reducing internal inductance
- · Package compatible with the conventional product\*
- Conventional product: Mitsubishi Electric NFH Series IGBT Modules

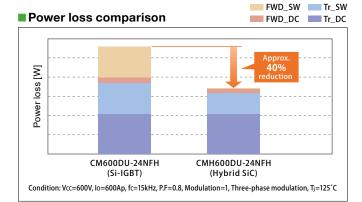
### ■ Product lineup

Applications	Model	Rated voltage	Rated current	Circuit configuration	External size (DxW)
	CMH100DY-24NFH		100A	2 in 1	48×94mm
	CMH150DY-24NFH		150A		48×94mm
	CMH200DU-24NFH	1200V	200A		62×108mm
Industrial equipment	CMH300DU-24NFH		300A		62×108mm
	CMH400DU-24NFH		400A		80×110mm
	CMH600DU-24NFH		600A		80×110mm
	CMH400HC6-24NFM		400A	1 in 1	62×108mm



#### ■ Recovery waveform (FWD)







3300V Full/SBD-embedded/Hybrid SiC Power Modules for Traction Inverters and HVDC system FMF185DC-66A / FMF375DC-66A / FMF800DC-66BEW

FMF750DC-66A / FMF750DC-66A-1 / CMH600DC-66X Commercially available

Contributes to energy saving and downsizing for inverters in traction motors, DC-power transmitters, large industrial machinery

#### ■ Features

[Full SiC]

- Suitable chip set combination for high speed switching
- ·Reduced power loss compared to the conventional products
- ·Low inductance package maximize SiC perfomance [SBD-embedded SiC]
- ·Adoption of SBD embedded SiC MOSFET have reduced switching losses compared to the conventional Full SiC
  - \* Si product: Mitsubishi Electric HVIGBT CM600DA-66X

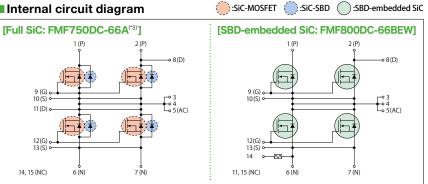
#### ■ Product lineup

	Model	Rated Voltage	Rated Current	Circuit configuration	External size (D x W)	
Full SiC	FMF185DC-66A		185A			
	FMF375DC-66A		375A			
	FMF750DC-66A		750A		100×140	
	FMF750DC-66A-1 (*1)	3300V	750A	2 in 1	mm	
SBD-embedded SiC-MOSFET	FMF800DC-66BEW*(*1,2)		800A			
Hybrid SiC	CMH600DC-66X	1	600A	l		

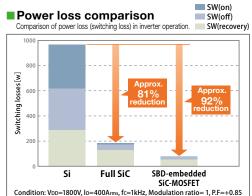
★: New product (\*1) Thermistor-equipped
(\*2) This product falls under item number 2 (41)3 of Appended Table 1 of the Export Trade Control Order.



#### ■ Internal circuit diagram



(\*3) Please refer to the data sheet for other model.





### 1700V/1200A Hybrid SiC Power Modules for Traction Inverters CMH1200DC-34S Commercially available

### High-power/low-loss/highly reliable modules appropriate for use in traction inverters

- · Power loss reduced approximately 30% compared to the conventional product\*
- · Highly reliable design appropriate for use in traction
- · Package compatible with the conventional product\*
- Conventional product: Mitsubishi Electric Power Module CM1200DC-34N

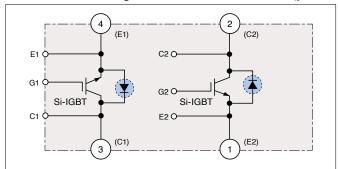
#### ■ Main specifications

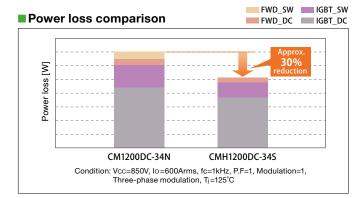
Max.operating te	emperature	150°C					
Isolation vo	oltage	4000Vrms					
Collector-emitter sati	2.3V						
Switching loss	turn-on	140mJ					
850V/1200V	turn-off	390mJ					
Emitter-collecto	2.3V						
Capacitive o	9.0µC						
	Isolation vo Collector-emitter sati Switching loss 850V/1200V Emitter-collector	Ovvitoriii ig 1000					

SiC-SBD:



#### ■Internal circuit diagram







### 600V/15A,25A Full SiC Super mini DIPIPM™ for Home Appliances PSF15S92F6-A6/PSF25S92F6-A6 Commercially available

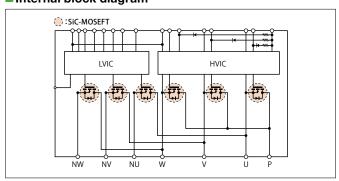
Contributes to extremely high power-efficiency in air conditioners, and easily applicable to industrial equipment

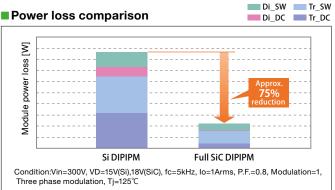
#### ■ Features

- · SiC-MOSFET achieves reduction in ON resistance, power loss reduced approx. 70% compared to conventional product\*
- · Construct low-noise system by reducing recovery current
- · Numerous built-in functions: Bootstrap diode for power supply to drive P-side, temperature information output, etc.
- · Unnecessary minus-bias gate drive circuit using original high Vth SiC-MOSFET technology
- · As package and pin layout compatibility with conventional products\* is ensured, simply replace with this product to improve performance \*Conventional product: Mitsubishi Electric Super mini DIPIPM Series



### ■Internal block diagram



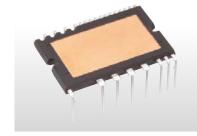




### Utilizing SiC enables high-frequency switching and contributes to reducing the size of peripheral components

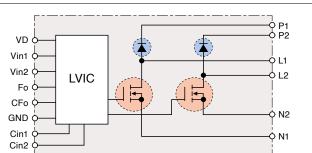
#### ■ Features

- Incorporating SiC chip in the Super mini package widely used in home appliances
- The SiC chip allows high-frequency switching (up to 40kHz) and contributes to downsizing the reactor, heat sink and other peripheral components
- Adopts the same package as the Super mini DIPIPM to eliminate the need for a spacer between the inverter and heat sink, and to facilitate its implementation

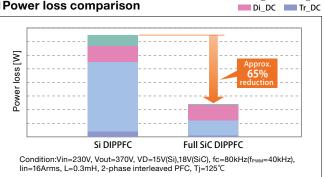


Di SW Tr SW

### ■ Internal block diagram (PSF30L92A6-A) :SIC-MOSFET :SIC-SBD



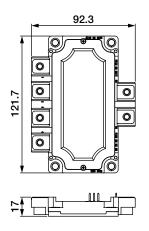
#### Power loss comparison



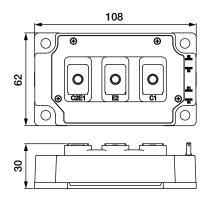
### ■Outline Drawing of SiC Power Modules

Unit:mm

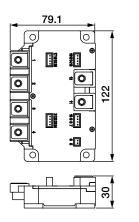




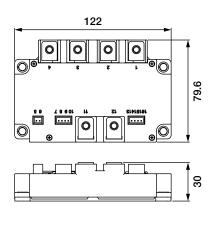
Full SiC Power Modules for Industrial Equipment FMF400DY-24B



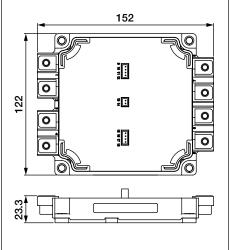
Full SiC Power Modules for Industrial Equipment FMF300BXZ-24B FMF400BXZ-24B



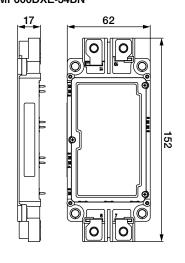
Full SiC Power Modules for Industrial Equipment FMF600DXZA-24B/FMF800DXZA-24B FMF300DXZ-34B/FMF300E3XZ-34B



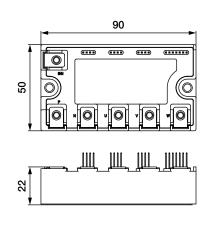
Full SiC Power Modules for Industrial Equipment FMF1200DXZ-24B



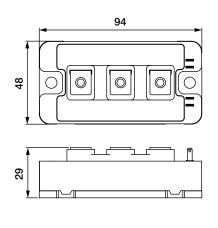
Full SiC power Modules for Industrial Equipment FMF600DXE-24BN FMF600DXE-34BN



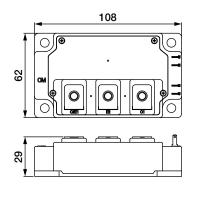
Full SiC IPM for Industrial Equipment PMF75CGA120 PMF75CGAL120



Hybrid SiC Power Modules for High-frequency Switching Applications CMH100DY-24NFH CMH150DY-24NFH



Hybrid SiC Power Modules for High-frequency Switching Applications CMH200DU-24NFH CMH300DU-24NFH



### ■Outline Drawing of SiC Power Modules

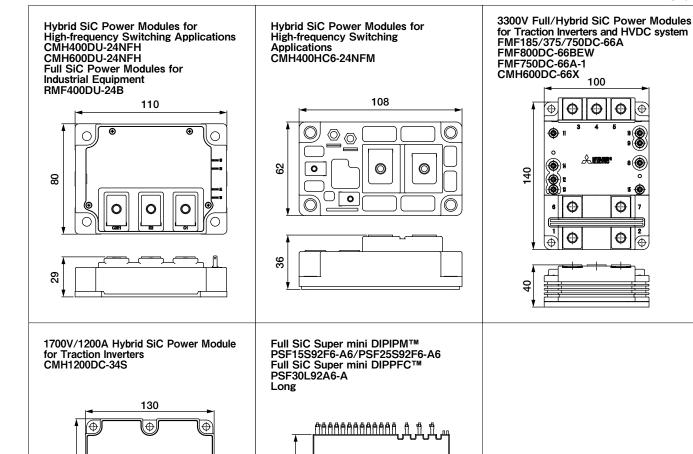
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Unit:mm



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Type Name LotNo.

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### Package, Main Application

Package		Main application
SOPIPM	-	Fan motor
SLIMDIP	_	Air conditioner/Fan motor/Washing machine/Refrigerator
Super mini	-	Air conditioner/Washing machine/Servo/Robot
Mini	<b>—</b>	Air conditioner/Motion control
Large	-	Commercial air conditioner/Motion control
DIPIPM+	-*-	Commercial air conditioner/Motion control
Large DIPIPM+	<del>-</del>	Commercial air conditioner/Motion control

### Data sheet here



### Rated Lineup

			Rated current										
		2A	5A	10A	15A	20A	25A	30A	35A	40A	50A	75A	100A
Rated	600V							•	-		*		
voltage	1200V			*			*		*			0	



### **Featured Products**

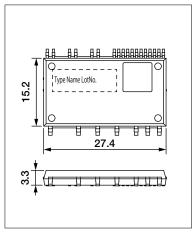


### Surface mount package IPM SOPIPM

# A small surface mount package IPM enables easy system design by enough insulation distance and protection function for fan and low-power motor drive applications

- <Main Features>
- •Optimal pin layout realizes easier PCB wiring design and enables smaller PCB size
- •Insulation distance between pins ensured, realizing easier board mounting without coating process
- •Newly integrated interlock function in addition to conventional protection features for robust operation
- •Installing RC-IGBT¹ simultaneously realizes compact package and low loss performance can go thogether
- •Bootstrap diode is integrated for the P-side drive power supply like conventional DIPIPM series, reducing the number of peripheral external parts

#### **■Outline Drawing**



#### **■**SOPIPM

Type name	Rated voltage	Rated current	Chips	Protection	Shape
SP2SK	600V	2A	RC-IGBT, HVIC, LVIC, BSD	UV, SC, OT VOT, IL	Surface mount package

[Term] UV : Power supply Under Voltage protection

SC : Short Circuit protection
OT : Over Temperature protection

 $\begin{array}{ll} \text{OT} : \text{Over Temperature protection} \\ \text{V}_{\text{OT}} : \text{Analog Temperature Output} \end{array}$ 

IL: Inter Lock

<sup>\*1</sup> Reverse-conducting IGBT



### **Featured Products**

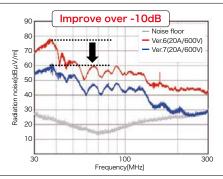
New design with expanded operating temperature range and lower noise contributes to easier system design and reduction in system cost

### Super Mini DIPIPM Ver.7

#### <Main Features>

- •New low-noise 7th-generation CSTBT\*1 incorporated, keeping same efficiency as DIPIPM Ver.6 Series. System cost reduction for noise suppression parts achieved.
- •Maximum junction temperature range expanded to 175°C, supporting instantaneous overcurrent capability at overload operation
- ·Wider terminal base shape contributes to improved terminal strength and suppresses increase in temperature
- ·High compatibility for terminal layout, easy to replace from the conventional series
  - \*1 CSTBT™: Mitsubishi Electric's unique IGBT that makes use of the carrier cumulative effect

### ■ Radiation noise





### **Featured Products**

**Expanded line up for SLIMDIP series contributes** system cost down for home appliances and fan drive application.

#### **SLIMDIP**<sup>TM</sup>

SLIMDIP-S, SLIMDIP-M, SLIMDIP-L, SLIMDIP-W, SLIMDIP-X, SLIMDIP-Z

#### <Main Features>

- •RC-IGBT\*1 incorporated, reducing package size 30% compared to Super mini DIPIPM
- ·Maximum case temperature expanded to 115°C, increasing the operating temperature range and leading to easier system design temperature range and leading to easier system design
- ·Additional terminals for floating supply and built-in bootstrap diodes simplify PCB wiring pattern
- •Both  $V_{\text{OT}}^{\text{-}2}$  and  $OT^{\text{-}3}$  functions integrated for temperature protection
- ·Expanded lineup accommodates wide-ranging inverter capacities
- \*1 Reverse conducting IGBT \*2 VoT : Analog Temperature Output \*3 OT : Over Temperature protection

## ■Wiring example

■ Product lineup

Fan, refrigerator

Air conditioner

Air conditioner

Type name

SLIMDIP-S

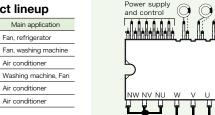
SLIMDIP-M

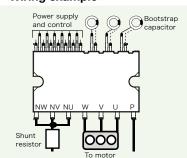
SLIMDIP-L

SLIMDIP-W

SLIMDIP-X

SLIMDIP-Z







### **Customer Support**

**EVA Series evaluation boards for each DIPIPM Series** to support system design



For Super mini DIPIPM **FVA11-SDIP** 



For DIPIPM+ EVA14-DIP+



For SOPIPM **FVA18-SOP** 



For Large DIPIPM Series (Microcomputer-embedded demonstration board) EVA20-LDIP

<sup>\*</sup> For further information, please contact sales office.

#### ■Series Matrix of 600V DIPIPM

	Vces				600V			
	Series		Super	mini	М	ini	Large	DIPIPM+
	Ic	SLIMDIP	Ver.7	Ver.6	Ver.7	_	Ver.6	CIB/CI
	5A	SLIMDIP-S		PSS05S92F6-AG PSS05S92E6-AG		PSS05S51F6		
	10A	SLIMDIP-M		PSS10S92F6-AG PSS10S92E6-AG		PSS10S51F6		
	15A	SLIMDIP-L SLIMDIP-W	PSS15S93F6-AG PSS15S93E6-AG	PSS15S92F6-AG PSS15S92E6-AG		PSS15S51F6		
	20A	SLIMDIP-X	PSS20S93F6-AG PSS20S93E6-AG	PSS20S92F6-AG PSS20S92E6-AG	PSS20S73F6	PSS20S51F6 PSS20S71F6		
	30A	SLIMDIP-Z*	PSS30S93F6-AG PSS30S93E6-AG	PSS30S92F6-AG PSS30S92E6-AG	PSS30S73F6	PSS30S71F6		
	35A			PSS35S92F6-AG PSS35S92E6-AG				
	40A		PSS40S93F6-AG PSS40S93E6-AG					
	50A				PSS50S73F6	PSS50S71F6	PSS50SA2F6	PSS50MC1F6 PSS50NC1F6*5
	75A						PSS75SA2F6	
	Chip	RC-IGBT	CSTBT	CSTBT	CSTBT	CSTBT	CSTBT	CSTBT
ص ح	UV	P-side/N-side	P-side/N-side	P-side/N-side	P-side/N-side	P-side/N-side	P-side/N-side	P-side/ N-side/ Brake
Protective Function	SC	N-side	N-side	N-side	N-side	N-side	N-side with sense	N-side
5 E S	OT	N-side	N-side*1	N-side*1	_	_	_	_
Ф.	Vот	N-side	N-side*1	N-side*1	N-side	N-side	N-side	N-side
	Active input	High(3/5V)	High(3/5V)	High(3/5V)	High(3/5V)	High(3/5V)	High(3/5V)	High(5V)
	Emitter pin of N-side	Open	Open	Open	Open	Open	Open	Open
Specifications	Fault output	N-side(UV,SC,OT)	N-side (UV,SC,OT)	N-side(UV,SC,OT)	N-side (UV,SC)	N-side (UV,SC)	N-side (UV,SC)	N-side (UV,SC)
sati	Insulation voltage	2000Vrms*2	1500Vrms*2	1500Vrms*2	2500Vrms	2500Vrms	2500Vrms	2500Vrms
ĭĊĬĖ	Insulation structure	Insulation sheet	Insulation sheet	Insulation sheet	Insulation sheet	Molding resin*4/Insulation sheet	Insulation sheet	Insulation sheet
Spe	RoHS directive*6	Compliant	Compliant	Compliant	Compliant	Compliant*3	Compliant	Compliant
	Pin type*7	Control side of Zigzag (Normal, Short)	Long	Long	Short	Control side of Zigzag, Short	-	_

★: New product

- [Notes] \*1: PSSxxS9xE6 has OT function, PSSxxS9xF6 has VoT function
  - \*2 : AC60Hz,1minute.Corresponds to isolation voltage 2500Vrms in the case the convex-shaped heat sink
  - $\*3$  : High melting point solder (Lead Over 85%) is used for chip soldering of PSSxxS51F6 only.

    \*4: Molding resin insulation for PSSxxS51F6/-C
  - \*5 : PSS50NC1F6 is not included brake.
  - \*6: RoHS directive (2011/65/EU and (EU) 2015/863)
  - $\ensuremath{\,\raisebox{.4ex}{$\star$}}\, 7$  : Refer the datasheet of each product for more detail

 $[\mathsf{Term}] \quad \mathsf{CSTBT}^{\mathsf{TM}}\!\!: \mathsf{Mitsubishi}\; \mathsf{Electric's}\; \mathsf{unique}\; \mathsf{IGBT}\; \mathsf{that}\; \mathsf{makes}\; \mathsf{use}\; \mathsf{of}$ 

the carrier cumulative effect RC-IGBT: Reverse conducting IGBT

HVIC: High Voltage IC

LVIC: Low Voltage IC

UV: Power supply Under Voltage protection

OT: Over Temperature protection

SC: Short Circuit protection Vot: Analog Temperature Output

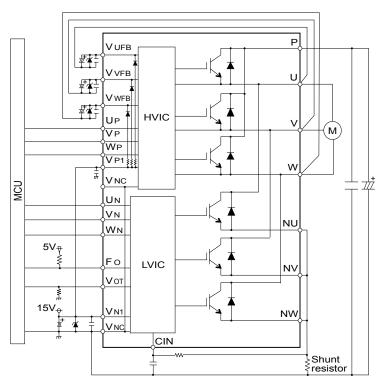
RoHS: Restriction of the use of certain Hazardous Substances

in electrical and electronic equipment

CIB: Converter Inverter Brake,

CI: Converter Inverter

### ■ Application circuit of super mini DIPIPM



### Lineup of DIPIPM™

#### ■ Series Matrix of 1200V DIPIPM

	Vces			1200V		
	Series	Mi	ni	Large	DIPIPM+	Large DIPIPM+
	Ic	Ver.7	_	Ver.6	CIB/CI	CI
	5A	PSS05S73FT	PSS05S72FT	PSS05SA2FT	PSS05MC1FT PSS05NC1FT*1	
	10A	PSS10S73FT	PSS10S72FT	PSS10SA2FT	PSS10MC1FT PSS10NC1FT*1	
	15A	PSS15S73FT		PSS15SA2FT	PSS15MC1FT PSS15NC1FT*1	
	25A	PSS25S73FT		PSS25SA2FT	PSS25MC1FT PSS25NC1FT*1	
	35A			PSS35SA2FT	PSS35MC1FT PSS35NC1FT*1	PSS35NE1CT*
	50A			PSS50SA2FT		PSS50NE1CT
	75A			PSS75SA2FT		PSS75NE1CT
	100A					PSS100NE1CT
	Chip	CSTBT	CSTBT	CSTBT	CSTBT	CSTBT
@ c	UV	P-side/N-side	P-side/N-side	P-side/N-side	P-side/N-side/Brake	P-side/N-side
Protective Function	SC	N-side	N-side	N-side	N-side	N-side
ote	OT	_	_	_	_	_
ÇΠ	Vот	N-side	N-side	N-side	N-side	N-side
	Active input	High(5V)	High(5V)	High(5V)	High(5V)	High(3/5V)
SI	Emitter pin of N-side	Open	Open	Open	Open	Open
atior	Fault output	N-side (UV,SC)	N-side (UV,SC)	N-side (UV,SC)	N-side (UV,SC)	N-side (UV,SC)
Specifications	Insulation voltage	2500Vrms	2500Vrms	2500Vrms	2500Vrms	2500Vrms
Sec	Insulation structure	Insulation sheet	Insulation sheet	Insulation sheet	Insulation sheet	Insulation sheet
Ϋ́	RoHS directive*2	Compliant	Compliant	Compliant	Compliant	Compliant
	Pin type	_	_	_	_	_

★: New Product

[Notes] \*1: PSS\*\*NC1FT is not included brake

 $\boldsymbol{*2}$ : RoHS directive (2011/65/EU and (EU) 2015/863)

[Term] CSTBT<sup>TM</sup>: Mitsubishi Electric's unique IGBT that makes use of the carrier cumulative effect

UV: Supply Under Voltage protection

OT: Over Temperature protection

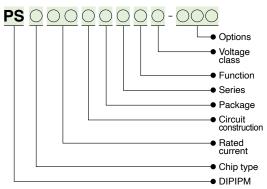
SC: Short Circuit protection Vor: Analog Temperature Output

RoHS: Restriction of the use of certain Hazardous Substances in electrical and electronic equipment

CIB: Converter Inverter Brake

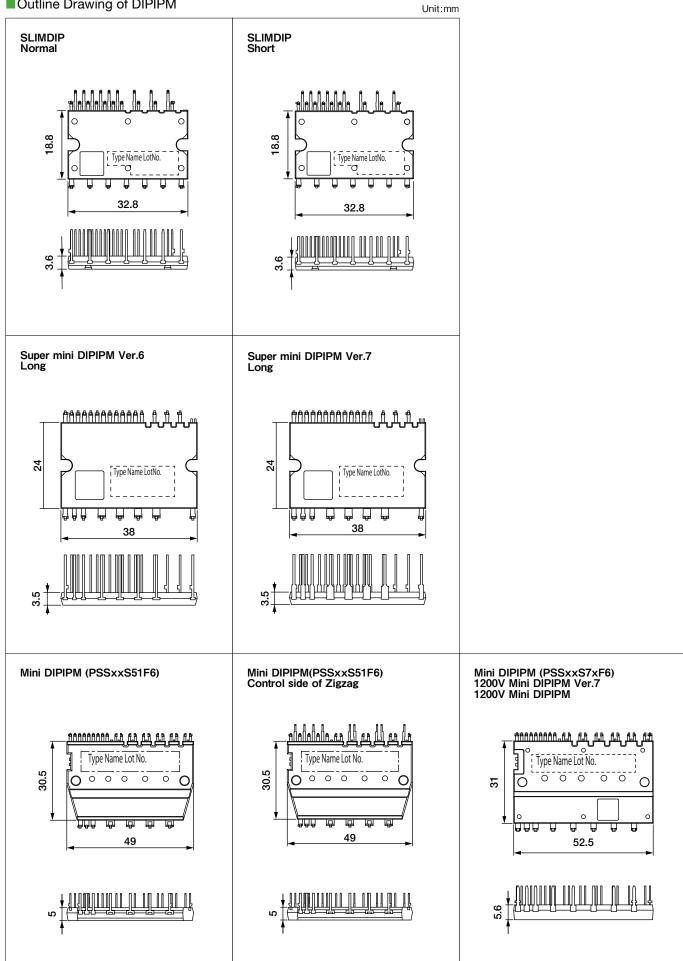
CI: Converter Inverter

### ■Type Name Definition of DIPIPM



### Lineup of DIPIPM™

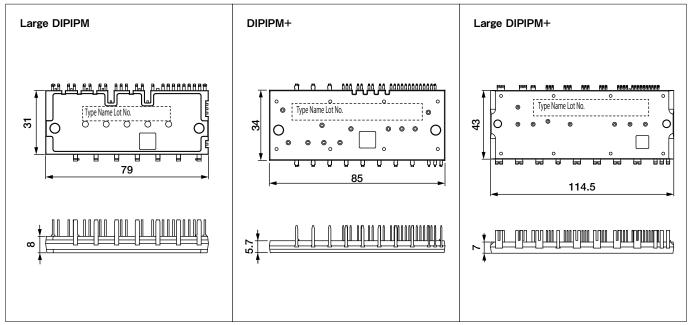




### Lineup of DIPIPM™

### ■Outline Drawing of DIPIPM

Unit:mm



### Series, Main Application

	Series	Main Application
G1	•	Motion control/Renewable energy/Power supply
V1	<b>—</b>	Motion Control/Nenewable energy/Fower supply

Data sheet here



### **Rated Lineup**

							Rat	ed curi	ent					
		25A	35A	50A	75A	100A	150A	200A	300A	400A	450A	500A	600A	800A
	600V									•				
Rated voltage	650V										•			
	1200V				•						•			



### **Featured Products**

Loaded with built-in functions, contributing to inverters with enhanced energy savings





- •Power loss has been reduced with the introduction of the 7th-generation IGBT produced using CSTBT™¹ and a diode incorporating a RFC¹² structure that contributes to reducing the power consumed in inverters
- •The new resin-insulated metal baseplate, originally introduced in 7th-generation IGBT modules, eliminates the solder-attached section, increasing the thermal cycle lifetime and improving inverter reliability
- In addition to the built-in functions of the previous product, automatic switching speed control, and error detection function contribute to lowering inverter loss and shortening design time
- \*1 CSTBT: Mitsubishi Electric's unique IGBT that utilizes the carrier cumulative effect
- \*2 RFC: Relaxed field cathode
- \*3 Conventional product: IPM L1-Series

Built-in functions: Supply Undervoltage lock protection (UV), Short-circuit protection (SC), Over-temperature protection (OT)

#### "A" package main pin shape and layout

For the "A" package 6-in-1 (CG1A) main pin shape, select either solder pin or screw type For the pin layout, select either straight or L-shaped

Main pin shape





Main pin: Solder pin

Main pin: Screw

Straight

L-shaped

### **Lineup of IPM**

#### ■ Matrix of IPM 650V/600V (No.: Number of outline drawing, see page 22)

Vces Series						
	G1 Series	Connection	65 No.	V1 Series	Connection	No.
Ic	2 22 22	CONTICCTION	110.		Connection	110.
	PM50CG1A065	С	06			
	PM50RG1A065	R	06			
	PM50CG1B065	С	04			
50A	PM50RG1B065	R	04			
JUA	PM50CG1AL065	С	06			
	PM50CG1AP065	С	03			
	PM50CG1APL065	С	03			
	PM50RG1AP065	R	03			
	PM75CG1A065	С	06			
	PM75RG1A065	R	06			
	PM75CG1B065	С	04			
	PM75RG1B065	R	04			
75A	PM75CG1AL065	С	06			
	PM75CG1AP065	C	03			
	PM75CG1APL065	C	03			
	PM75RG1AP065	R	03			
	T WY GITCHAN GOO	''	00			
	PM100CG1A065	С	06			
	PM100CG1R065	C	04			
		R	04			
100A	PM100RG1B065					
	PM100CG1AL065	С	06			
	PM100CG1AP065	С	03			
	PM100CG1APL065	С	03			
	PM150CG1B065	С	04			
150A	PM150RG1B065	R	04			
	PM200CG1B065	С	04			
200A	PM200RG1B065	R	04			
2004	PM200CG1C065	С	05			
	PM200RG1C065	R	05			
300A	PM300CG1C065	С	05			
400A	PM300RG1C065	R	05	PM400DV1A060	D	01
	PM450CG1C065	С	05			
450A	PM450RG1C065	R	05			
600A				PM600DV1A060	D	01
800A				PM800DV1B060	D	02
IGBT	CSTBT*1			CSTBT*1		
chip	Built-in emitter sensor			Built-in emitter sensor		
J. 115	Built-in temperature sensor			Built-in temperature sensor		
UV	P-side/N-side			P-side/N-side		
Fault OT	P-side/N-side			P-side/N-side		
output SC	P-side/N-side			P-side/N-side		
Identification	P-side/N-side			_		
RoHS directive*2				Compliant		
	Compliant			V Series		
Compatibility						
	D B4 B4	5 ← 📘		C R R	l <sub>l</sub>	
Connection		Ĵ.	~\J.		¥	
	ok_t	~  <b>\</b>	~[스̄		Ť,	
	~ •	• -				

[Notes] \*1: Full-gate CSTBT™

\*2: RoHS directive (2011/65/EU and (EU) 2015/863)

[Term] CSTBT™: Mitsubishi Electric's unique IGBT that makes use of the carrier cumulative effect

UV: Power supply Under Voltage protection

SC: Short Circuit protection
OT: Over Temperature protection

RoHS: Restriction of hazardous substances in electrical and electronic equipment

### **Lineup of IPM**

### ■ Matrix of IPM 1200V (No.: Number of outline drawing, see page 22)

Vces			120	00V		
Series	G1 Series	Connection	No.	V1 Series	Connection	No.
	PM25CG1A120	С	06			
	PM25CG1B120	С	04			
	PM25RG1A120	R	06			
	PM25RG1B120	R	04			
25A	PM25CG1AL120	С	06			
	PM25CG1AP120	С	03			
	PM25CG1APL120	С	03			
	PM25RG1AP120	R	03			
	PM35CG1A120	С	06			
	PM35CG1B120	С	04			
	PM35RG1A120	R	06			
054	PM35RG1B120	R	04			
35A	PM35CG1AL120	С	06			
	PM35CG1AP120	С	03			
	PM35CG1APL120	С	03			
	PM35RG1AP120	R	03			
	PM50CG1A120	С	06			
	PM50CG1B120	С	04			
	PM50RG1B120	R	04			
50A	PM50CG1AL120	С	06			
	PM50CG1AP120	С	03			
	PM50CG1APL120	C	03			
75A	PM75CG1B120 PM75RG1B120	C R	04 04			
	PM100CG1B120	С	04			
	PM100CG1C120	C	05			
100A						
	PM100RG1B120	R	04			
	PM100RG1C120	R	05			
4504	PM150CG1C120	С	05			
150A	PM150RG1C120	R	05			
200A	PM200CG1C120 PM200RG1C120	C R	05 05	PM200DV1A120	D	01
300A				PM300DV1A120	D	01
450A				PM450DV1A120	D	01
IGBT chip	CSTBT*1 Built-in current sensor Built-in temperature sensor			CSTBT*1 Built-in current sensor Built-in temperature sensor		
UV	P-side/N-side			P-side/N-side		
Fault OT	P-side/N-side			P-side/N-side		
output SC	P-side/N-side			P-side/N-side		
Identification	P-side/N-side				+	
RoHS directive*2	Compliant			Compliant	+	
Compatibility	—			V Series		
	D C J		1.4.	1 551135		
Connection				<u> </u>		

 $\hbox{[Term]} \quad \hbox{CSTBT}^{\text{\scriptsize TM}}\hbox{: Mitsubishi Electric's unique IGBT that makes use of the carrier cumulative effect}$ 

UV: Power supply Under Voltage protection SC: Short Circuit protection OT: Over Temperature protection

RoHS: Restriction of the use of certain Hazardous Substances in electrical and electronic equipment

### **Lineup of IPM**

■Outline Drawing of IPM

02 03 PM400,600DV1A060 PM200,300,450DV1A120 PM800DV1B060 PM50,75,100CG1AP/CG1APL065 PM50,75RG1AP065 PM25,35,50CG1AP/CG1APL120 PM25,35RG1AP120 120 120 **●**(○ 90 Ō, 90 20 20 0  $( \bigcirc$ 0 0 0 O 0 0 34 04 05 06 PM200,300,450CG1C/ RG1C065 PM100,150,200CG1C/ RG1C120 PM50,75,100CG1A/CG1AL065 PM50,75RG1A065 PM25,35,50CG1A/CG1AL120 PM25,35RG1A120 PM50,75,100,150,200CG1B/ RG1B065 PM25,35,50,75,100CG1B/ RG1B120 120 120 90 0 ••• ••• • ••••• 0 @····]||····||||····|| 0 O 55 @····||||····||||····|| 85 0  $(\bigcirc$ 20 0 0 [O] u O v 0 0 <u>^\_\_\_\_\_\_\_\_</u> 22 22

Unit:mm

### Series, Main Application

Series		Main Application
Т	-	
T1	_	
TH	-	Motion control/Renewable energy /Power supply
For 3-level Inverters	<b>—</b>	
S	-	

Data sheet here



### **Rated Lineup**

									Rate	d cur	rent							
		35A	50A	75A	100A	150A	200A	225A	300A	400A	450A	500A	600A	800A	900A	1000A	1200A	1400A
	650V			4						•			•					
											-		<b>—</b>					
Rated	1200V			<u> </u>			-			_			_					<b>-</b>
voltage																		
	1700V			_		_			-		-					-		
	2000V						•			•							•	



### **New Products**

Industrial IGBT module with new standard package "LV100" for high power density inverter

### IGBT module T-series (LV100 for industrial)

IGBT module 2in1 type

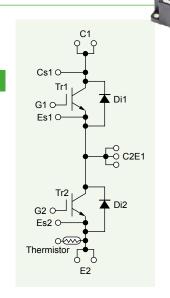
#### Lineup

1200A/2000V

800A/1700V, 800A/1700V(with enhanced FWD), 1200A/1700V 800A/1200V, 1200A/1200V

#### $\langle \text{Main Features} \rangle$

- •Next generation high capacity standard package for industrial use
- ·Improved ease of use by applying low impedance package
- $\cdot$ Reducing the switching loss and optimal for the applications that are used in 1 to 5KHz
- ·Isolation voltage 4kV





### **Featured Products**

New lineup contributes to simple design downsizing, energy-savings of industrial inverters.

### IGBT Module T/T1-Series

- <Main Features>
- New modules equipped with three-phase converter, inverter, and brake circuit(CIB), contributes to simplifying design for inverter systems
- •CIB modules contribute to compact inverter systems by reducing package size by 36% compared to the Mitsubishi Electric's existing module.(CIB)
- Power loss has been reduced with the introduction of the 7th-generation IGBT produced using CSTBT<sup>2</sup> and a diode incorporating a relaxed field of cathode (RFC) structure
- The new structure introduced eliminates the solder-attached section, increasing the thermal cycle lifetime, which contributes to improving the reliability of inverters
- The introduction of press-fit pins and PC-TIM\* contribute to simplifying the assembly process for inverters
- \*1 PC-TIM: Phase change thermal interface material \*2 CSTBT: Mitsubishi Electric's unique IGBT that makes use of the carrier cumulative effect

#### ◆ Press-fit terminal support (NX)

- Possible to select the control pin shape (soldered terminals/press-fit terminals)
- Solder attachment process eliminated



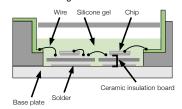




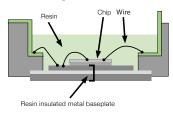
ain pin ②Signal p

### New structure realizes improved reliability (improved thermal cycle lifetime)

### NX package structure comparison 6th-generation IGBT

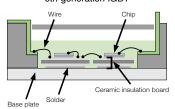


7th-generation IGBT

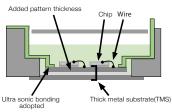


\*\*Adopts SoLid Cover(SLC) Technology

### Compared to standard (std) package structure 6th-generation IGBT



#### 7th-generation IGBT



\*Standard package is not available for CIB

# **1**6

### **Featured Products**

Low switching loss contributes to efficiency improvement of industrial inverters during high-frequency operation.

TH-series IGBT Modules with 7th-generation IGBT for High-frequency switching applications

#### <Main Features>

- •A chip optimized for high-frequency applications fc target 20-60kHz
- •High-speed specifications reduce power consumption during high-frequency switching. The loss is reduced by about 30% compared to general specifications\*1
- Lineup of 1200V 200A to 600A (2 types of packages are available for 400A)
- \*1:7th-generation T series with general specifications

#### ■Package



48 x 94mm 1200V/200A •CM200DY-24TH



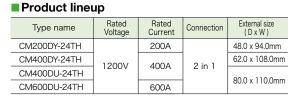
62 x 108mm 1200V/400A •CM400DY-24TH



80 x 110mm 1200V/400A,600A •CM400DU-24TH

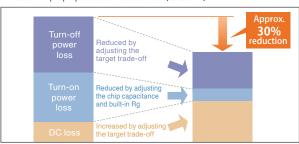
•CM600DU-24TH

### . 1



#### ■ Power loss comparison

Note: Example properties of TH-series IGBT(fc=30kHz)



general specifications 7th-generation T-series High-speed specifications 7th-generation TH-series

■ Matrix of IGBT Modules 650V/600V (No.: Number of outline drawing, see page 28 to 32)

RoHS directive (2011/65/EU, (EU)2015/863) compliant

Vces			65	OV			600V	3,2010,000,0	
Series	T/T1-Series			T-Series			NFH-Series		
Ic	NX Type Co	nnection	No.	std Type Co	onnection	No.	Ni 11-3enes	Connection	No.
50A	CM50MXUB-13T CM50MXUB-13T1 CM50MXUBP-13T CM50MXUBP-13T1	M M M	32 32 36 36						
75A	CM75MXUB-13T CM75MXUB-13T1 CM75MXUBP-13T CM75MXUBP-13T1	M M M	32 32 36 36						
100A	CM100TX-13T CM100TXP-13T CM100MXUB-13T CM100MXUB-13T1 CM100MXUBP-13T CM100MXUBP-13T1 CM100MXUD-13T1 CM100MXUD-13T1 CM100MXUD-13T1 CM100MXUDP-13T1	T M M M M M M	24 27 32 32 36 36 34 34 38 38	CM100DY-13T	D	19			
150A	CM150TX-13T CM150TXP-13T CM150RX-13T CM150RXP-13T CM150MXUD-13T CM150MXUD-13T1 CM150MXUDP-13T CM150MXUDP-13T1	T T R R M M	24 27 25 28 34 34 38 38	CM150DY-13T	D	19			
200A	CM200TX-13T CM200TXP-13T CM200RX-13T CM200RXP-13T	T T R R	24 27 25 28	CM200DY-13T	D	19	CM200DU-12NFH	D	11
300A	CM300DX-13T CM300DXP-13T	D D	17 29	CM300DY-13T	D	20	CM300DU-12NFH	D	12
400A				CM400DY-13T	D	20	CM400DU-12NFH	D	12
450A	CM450DX-13T CM450DXP-13T	D D	17 29						
600A	CM600DX-13T CM600DXP-13T	D D	17 29	CM600DY-13T	D	21	CM600DU-12NFH	D	13
Connection	D	Т		R		M			

Matrix of Power Modules for 3-level Inverter (No.: Number of outline drawing, see page 28 to 32)

BoHS directive (2011/65/EU. (EU)2015/863) compliant

							- ' ' ' ' ' ' ' '	RoHS d	irective	e (2011/65/EU, (EU)2015	5/863) com	npliant
Vces/Vrrm	1200 V IGBT	Module		1700 V IGBT Mo	dule		1200 V Diode M	odule		1700 V Diode	Module	
lc/lF	T/S-Series std Type	Connection	No.	S-Series std Type	nnection	No.	S-Series std Type	Connection	No.	S-Series std Type	Connection	No.
200A	CM200ST-24T*	s	40									
400A	CM400ST-24T*	s	40									
400A	CM400C1Y-24S	C1	09									
450A	CM450C1Y-24T	C1	21									
500A	CM500C2Y-24S	C2	26									
600A	CM600C1Y-24T	C1	21	CM600HA-34S	Н	26				RM600DY-34S	D	22
A008				CM800HA-34S	Н	26				RM800DY-34S	D	22
1000A				CM1000HA-34S	Н	26						
1400A	CM1400HA-24S	Н	26				RM1400HA-24S	Н	26			
Connection	IGBT module C		C2	H S			Diode n	module	Н	D O		

■ Matrix of IGBT Modules 1200V (No.: Number of Outline Drawing, see page 28 to 32)

RoHS directive (2011/65/EU, (EU)2015/863) compliant

Vces										1200V			กบทอน	1160	LIVE	(2011/03/E0	), (I	LO)	2015/863) cor	Прі	anı
Series	T-Series LV10	O T	ype	T/T1-Series NX	( T	ype	T-Series std Ty	/pe	)	TH-Series			S-Series NX T	уре	)	S-Series std T	ype	)	S-Series MPD	Ту	ре
lc \	Connec	tion	No.	Connect			Connect	tion	No.	Connec	tion	No.	Connec	tion	No.	Connec	tion	No.	Connect	tion	No.
35A				CM35MXUA-24T1 CM35MXUAP-24T	M M	31 31 35 35							CM35MXA-24S	М	03						
50A				CM50MXUAP-24T	Μ	31 31 35 35							CM50MXA-24S	М	03						
75A				CM75MXUC-24T CM75MXUC-24T1 CM75MXUCP-24T	M M M M	32 36							CM75TX-24S CM75RX-24S CM75MXA-24S	R	04 01 03						
100A					T R R M M	25 28 33 33 37	CM100DY-24T	D	19				CM100MXA-24S	М	03						
150A					T R R M M	25 28 34 34 38	CM150DY-24T	D	19				CM150DX-24S CM150EXS-24S		02 16						
200A				CM200TX-24T CM200TXP-24T	T T	24 27	CM200DY-24T	D	20	CM200DY-24TH	D	06	CM200DX-24S CM200RXL-24S CM200EXS-24S	R	02 15 16						
225A				CM225DX-24T CM225DX-24T1 CM225DXP-24T CM225DXP-24T1	D D D	17 29															
300A				CM300DX-24T CM300DX-24T1 CM300DXP-24T CM300DXP-24T1	D D	29	CM300DY-24T	D	20				CM300EXS-24S	Е	16	CM300DY-24S	D	07			
400A										CM400DY-24TH CM400DU-24TH		08 13									
450A				CM450DXP-24T	D D D	17 17 29 29	CM450DY-24T	D	21							CM450DY-24S	D	09			
600A					D D D	17 17 29 29	CM600DY-24T	D	21	CM600DU-24TH	D	13	CM600DXL-24S	D	05	CM600DY-24S	D	09			
800A	CM800DW-24T	D	39	CM800DX-24T1 CM800DXP-24T1	D	17 29										CM800DY-24S	D	10			
900A				5.MOOODA1 -2411		23													CM900DUC-24S	D	14
1000A				CM1000DX-24T CM1000DXP-24T	D D	18 30							CM1000DXL-24S	D	05						
1200A	CM1200DW-24T	D	39	T.I.I.OODJAI ETI	_																
1400A																CM1400HA-24S	Н	26	CM1400DUC-24S	D	14
Connection	H		D	T	اله اله		R		<u>_</u>			М		3-4		E		• •	E3	•	

 $<sup>{\</sup>rm *1: A-Series \; have \; model \; namse \; ending \; with \; A, \; NF-Series \; have \; model \; name \; ending \; with \; NF/NFH}$ 

<sup>\*2:</sup> std Type have model name "CM\*\*DY/HA-24S, MPD Type have model name "CM\*\*DUC-24S"

■ Matrix of IGBT Modules 1700V (No.: Number of Outline Drawing, see page 28 to 32)

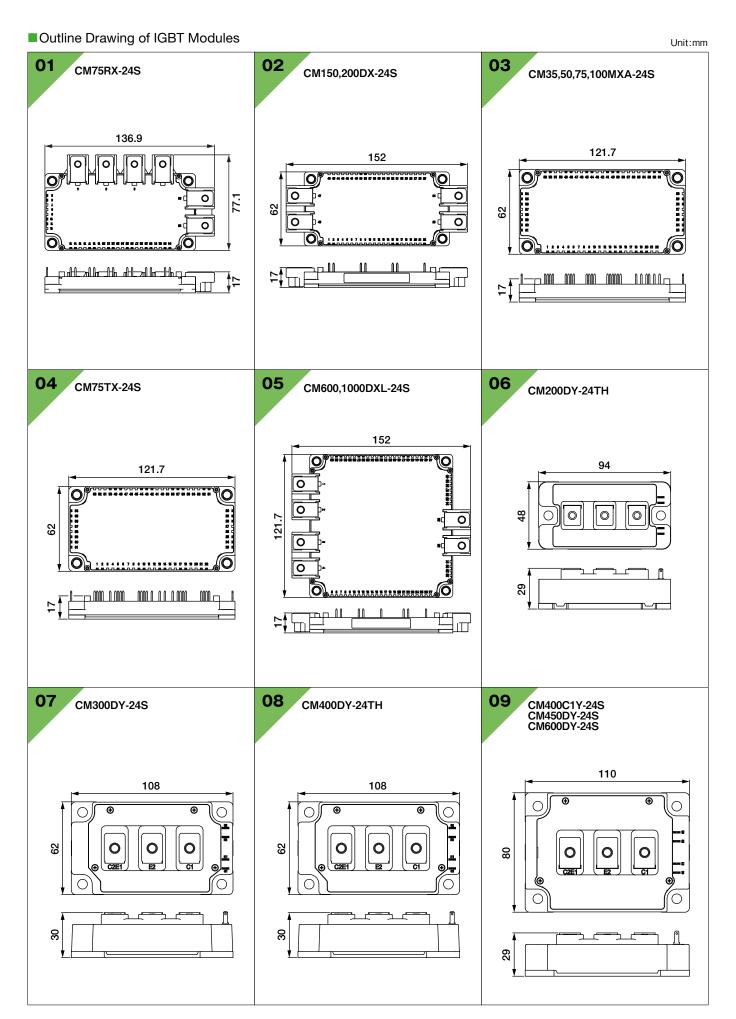
RoHS directive (2011/65/EU, (EU)2015/863) compliant

Vces								170	0V							
Series	T-Series				T-Series				T-Series				S-Series			
lc \	LV100 Type	Conne	ction	No.	NX Type	Connec	ction	No.	std Type	Connec	tion	No.	std Type	Connec	tion	No.
75A									CM75DY-34T		D	19				
100A					CM100TX-347 CM100TXP-34		T T	24 27	CM100DY-34T		D	19				
150A					CM150TX-347 CM150TXP-34		T T	24 27	CM150DY-34T		D	20				
200A									CM200DY-34T		D	20				
225A					CM225DX-34 <sup>-</sup> CM225DXP-3-		D D	17 29								
300A					CM300DX-34 <sup>-</sup> CM300DXP-34		D D	17 29	CM300DY-34T		D	21				
400A									CM400DY-34T		D	21				
450A					CM450DX-34 <sup>-</sup> CM450DXP-34		D D	17 29								
500A																
600A					CM600DX-34 <sup>-</sup> CM600DXP-34		D D	17 29					CM600HA-345	8	Н	26
800A	CM800DW-34 CM800DW-34		D D	39 39									CM800HA-345	8	Н	26
1000A													CM1000HA-34	ıs	Н	26
1200A	CM1200DW-3	34T	D	39												
Connection	H A		D م ا		T		R 。	- L	M				E			

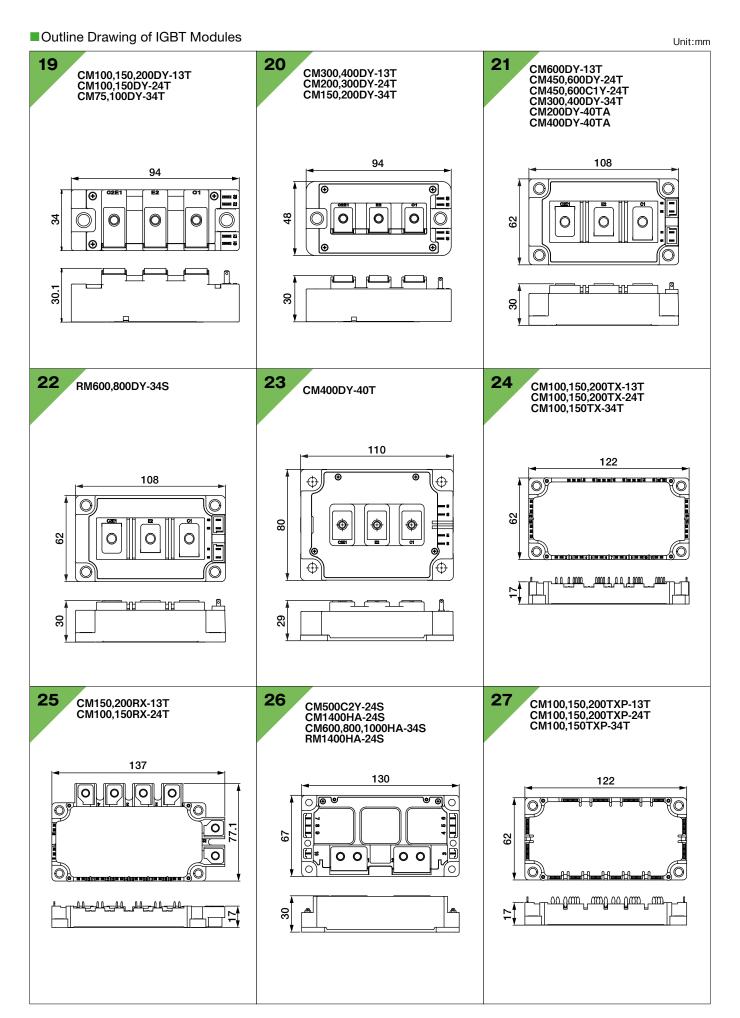
### ■ Matrix of IGBT Modules 2000V (No.: Number of Outline Drawing, see page 28 to 32)

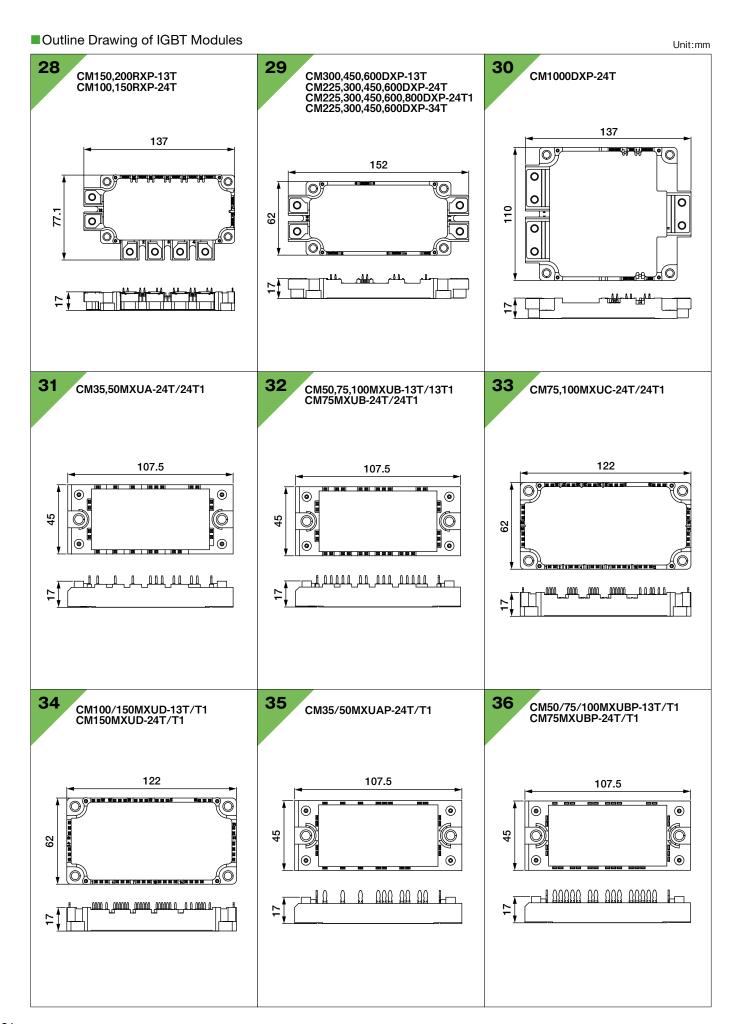
RoHS directive (2011/65/EU, (EU)2015/863) compliant

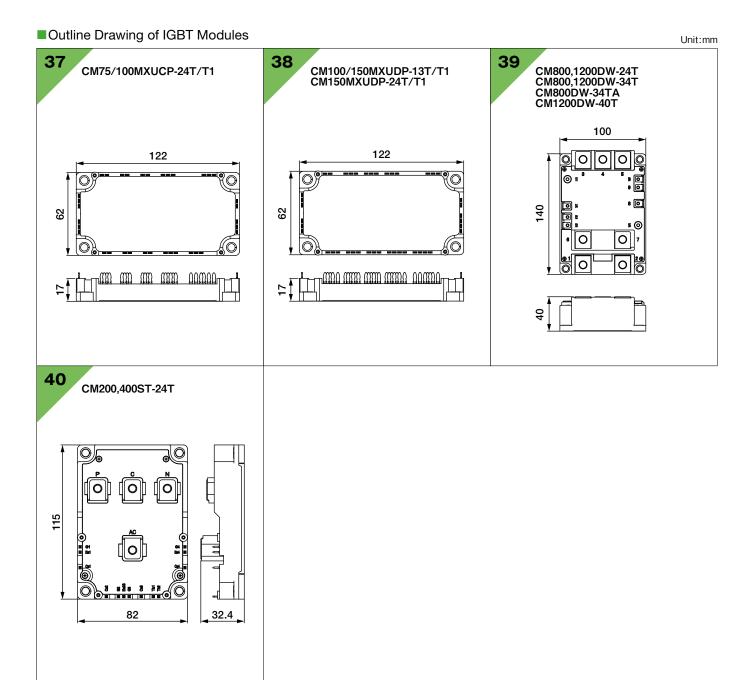
								ip.i.ci.it
Vces				200	V00			
Series	T-Series				T-Series			
lc \	LV100 Type	Connec	ction	No.	std Type	Conne	ction	No.
200A					CM200DY-40T	A	D	21
400A					CM400DY-40T CM400DY-40T		D D	23 21
1200A	CM1200DW-40	TC	D	39				
Connection				D الہ الہ				



■Outline Drawing of IGBT Modules Unit:mm CM300,400DU-12NFH CM800DY-24S CM200DU-12NFH **⊕** E2 O CM600DU-12NFH CM400,600DU-24TH CM900,1400DUC-24S CM200RXL-24S 136.8 • Œ Ы CM150EXS-24S CM200EXS-24S CM300EXS-24S CM300,450,600DX-13T CM1000DX-24T CM225,300,450,600DX-24T CM225,300,450,600,800DX-24T CM225,300,450,600,800DX-24T1 CM225,300,450DX,600DX-34T O <u>o</u> O) O, llo. 







### Package, Main Application

	Series	Main Application
X	-	
R	_	
S	-	Traction/Power transmission/Motion control
N	<b>—</b>	
Н	-	

Data sheet



### Rated Lineup

		Rated current													
		200A	400A	450A	600A	800A	900A	1000A	1200A	1350A	1500A	1600A	1800A	2400A	
	1700V					<b>—</b>			-				-	•	
Rated voltage	3300V					_					_		•		
	4500V			•			-								
	6500V				•										



#### X Series HVIGBT Modules std type





- •Power loss reduced by incorporating 7th-generation IGBT and RFC<sup>-1</sup> diode
- •Compared to the existing CM900HC-90H and CM1350HC-90X, the new models' rated output currents are 50% greater but external dimensions are
- •Compared to existing CM900HC-90H, new CM900HC-90X, etc. are 33% smaller but achieve the same voltage and current ratings.
- •Optimal package internal structure realizes improved heat dissipation, humidity resistance and flame retardance, increasing product life

### ■ Product lineup

std type	1.7kV	3.3kV	4.5kV	6.5kV
	2400A	1200A	900A 1000A	600A
	2400A	1200A 1800A	900A 1350A 1500A	600A 900A 1000A

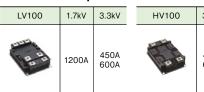
### X Series HVIGBT Modules dual type

### New common frame package: dual type class-leading current density contributes to increased power output in inverter systems



- ullet Power loss reduced by incorporating 7th-generation IGBT and RFC  $^{*1}$  diode
- Industry's highest 3.3kV/600A Si module power density of 8.57A/cm<sup>2</sup> \*2 contributes to increased power output and efficiency
- •Terminal layout optimized for easy paralleling and flexible inverter configurations and capacities
- ·New package structure offers extra reliability
  - \*2 As of Dec. 17, 2020 based on Mitsubishi Electric research

#### ■ Product lineup



HV100	3.3kV	4.5kV
	450A 600A	450A

<sup>\*1</sup> RFC : Relaxed field of cathode

### ■ Series Matrix of HVIGBT (No.: Number of Outline Drawing, see page 36)

Vces					1700	V							3300V											
Ic VCES	X-Series				S-Series N-Series				H-Series				X-Series				R-Series				H-Series			
10	Conne	ction	Туре	No.	Conne	ction	Туре	No.	Conne	ction	Туре	No.	Conne	ction	Туре	No.	Conne	ction	Туре	No.	Conne	ection	Туре	No.
400A																					CM400HG-66H CM400DY-66H	H D1	G B1	06
450A													CM450DA-66X CM450DE-66X CM400HG-66X**	D2 D2 H	A E G	07 08 09								
600A									CM600DY-34H CM600E2Y-34H	D1 E2	B2 B2	01 01	CM600DA-66X CM600DE-66X CM600E1A-66X	D2 D2 E1	A E A	07 08 07								
800A					CM800DZB-34N	D1	C2		CM800DZ-34H	D1	C2	-									CM800HC-66H CM800E4C-66H CM800E6C-66H	H E4 E2	C1 C1 C1	- - -
1000A																	CM1000HC-66R CM1000E4C-66R	H E4	C1 C1	- -				
1200A	CM1200DA-34X	D2	Α	07	CM1200HCB-34N CM1200DC-34N CM1200E4C-34N CM1200DC-34S CMH1200DC-34S	וטן	C2	-	CM1200HC-34H	Н	C2	_	CM1200HC-66X CM1200HCB-66X CM1200E4C-66X**	H H E4	C1 C1 C1	02 03 03					CM1200HC-66H CM1200HG-66H	H	C1 C1	
1500A																	CM1500HC-66R	Н	C1	-				
1600A									CM1600HC-34H	Н	C2	-												
1800A					CM1800HC-34N CM1800HCB-34N	H	C2 C2	-	CM1800HC-34H	Н	C2	-	CM1800HC-66X CM1800HG-66X	H	C1 G	03 04								
2400A	CM2400HC-34X CM2400HCB-34X	ΗH	C1 C1	02 03	CM2400HC-34N CM2400HCB-34N	H	C2 C2	-	CM2400HC-34H	Н	C2	03												
Connection			!	Н 。		≣1			E2/E6	, 7,	- - - - - - - - - - - - - - - - - - -		E4	0000		D	1	-	D2		~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~			

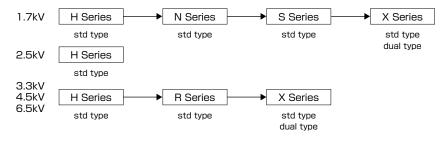
[Type]
A:Al base plate 6kV Isolation
B1:Cu base plate / 6kV Isolation
B2:Cu base plate / 4kV Isolation

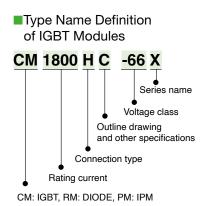
E:Al base plate 10kV Isolation

B2:Cu base plate / 4kV Isolation C1:AISiC base plate / 6kV Isolation C2:AISiC base plate / 4kV Isolation G:AISiC base plate 10kV Isolation ★★: Under development
The outline drawing is written the figure of principal part numbers that have a common dimension.

Non-recommended: Please contact to the sales offices.

#### ■ Evolution of HVIGBT Module Series





### ■ Series Matrix of HVIGBT (No.: Number of Outline Drawing, see page 36)

Vces					4500	V						6500V								
Ic VCLS	X-Series				R-Series				H-Series				X-Series				H-Series			
10	Conne	ction	Туре	No.	Conne	ction	Туре	No.	Conne	ction	Туре	No.	Conne	ction	Туре	No.	Conne	ction	Туре	No.
200A																	CM200HG-130H	Н	G	-
400A																	CM400HG-130H CM400E2G-130H CM400E4G-130H	H E2 E4	G G	
450A	CM450DE-90X*	D2	Е	08																L
600A									СМ600НG-90Н	Н	G	05	CM600HG-130X	Н	G	05	CM600HG-130H	Н	G	-
800A					CM800HC-90R CM800HG-90R	H	C1 G	02 05												
900A	CM900HC-90X CM900HG-90X CM900E2G-90X	H H E2	C1 G G	02 05 04					СМ900НС-90Н СМ900НG-90Н	Н	C1 G		CM900HG-130X	Н	G	04				
1000A	CM1000HG-90X	Н	G	05									CM1000HG-130XA	Н	G	04				
1200A					CM1200HC-90RA CM1200HG-90R	H	C1 G	-												
1350A	CM1350HC-90X CM1350HG-90X	H	C1 G	03 04																
1500A	CM1500HC-90XA CM1500HG-90X	HH	C1 G	03 04																
Connection					H ~	尤		E	52	E4			D2							_

[Type]
A:Al base plate 6kV Isolation
B1:Cu base plate / 6kV Isolation
B2:Cu base plate / 4kV Isolation
C1:AISiC base plate / 6kV Isolation
C2:AISiC base plate / 6kV Isolation
G:AISiC base plate / 4kV Isolation
G:AISiC base plate 10kV Isolation
E: Al base plate 10kV Isolation

★: New product

The outline drawing is written the figure of principal part numbers that have a common dimension.

Non-recommended: Please contact to the sales offices.

■Outline Drawing of HVIGBT Modules Unit:mm 02 03 CMH1200DC-34S CM2400HC-34X CM1200HC-66X CM900HC-90X CM2400HCB-34X, CM1200HCB-66X, CM1800HC-66X, CM1350HC-90X, CM1500HC-90XA CM600DY/E2Y-34H 130 190 130 (<del>+</del>) (III)  $\oplus$ ] 1 ] [  $\Phi$  $\oplus$ [ ]\. **• ⊕**]4 **⊕**]2  $\bigoplus$  $\oplus$ Ф **⊕** |2 4 140 **4 ⊕** ]3  $\oplus$ 1 **(**) (a)  $\bigoplus$ ](1)[ ](1)[ ](1) (<del>-</del> ](1) ]( 04 05 06 CM900, 1000HG-90X CM800HG-90R CM600HG-90H/130X CM1800HG-66X, CM900E2G-90X CM1350HG-90X, CM1500HG-90X CM900HG-130X, CM1000HG-130XA CM400DY-66H 130 130 190  $\Phi$  $\oplus$  $\overline{\Phi}$ ) <del>(</del>  $(\oplus)$  $\mathbb{Q}$  $\Phi$ **( (** Ф Ф **( ( (**)2 6 140 CM C1  $\oplus$ E2 Ф  $\oplus$ **( ⊕**]• **(** lacktriangledown**(4) (4) ⊕** E (A) **( ( (** 07 08 09 CM450DE-66X, CM600DE-66X CM450DE-90X CM1200DA-34X CM450DA-66X, CM600DA-66X, CM600E1A-66X CM400HG-66X 100 100 0 剦  $\oplus$ Ф Ф Φ lacksquare8 🐠 140 4 9 (D) 10 (D)  $\bigcirc$ (4) Ф  $\oplus$ 0 Φ  $\oplus$ 48

### **HVDIODE Modules**

### Series, Main Application

Series		Main Application
HVDIODE Modules	•	Traction/Power transmission/Motion control

### Data sheet



### **Rated Lineup**

						Rat	ed curr	ent				
		300A	400A	450A	600A	750A	800A	900A	1000A	1200A	1500A	1800A
	1700V									•		•
Rated	3300V		•		-					•		
voltage	4500V			•			•					
	6500V	•							-			

#### ■ Series Matrix of HVDIODE Modules (No.: Number of outline drawing, see page 38)

V <sub>PRM</sub>	1700V		I	1	3300V		I		4500V		-		6500V			
300A	Connec	ction	Туре	No.	Conne	ection	Туре	No.	Connec	ction	Туре	No.	RM300DG-130X	D	Type G	10
						_	_						RIVISUUDG-13UX	0	<u>u</u>	10
400A					RM400DG-66S RM400DY-66S	D D	G B	-								
450A									RM450DG-90X	D	G	10	RM450DG-130X	D	G	10
600A					RM600DY-66S	D	В	-					RM600DG-130S	D	G	10
OOOA					RM600DC-66X	D	С	11					RM600DG-130X	D	G	10
750A									RM750DC-90X**	D	С	11				
800A									RM800DG-90F	D	G	10				
900A									RM900HC-90S RM900DB-90S	H	C B	- 11				
									RM900DG-90X	D	G	10				
1000A					RM1000DC-66F	D	С	-					RM1000DG-130XA	D	G	10
1200A	RM1200DB-34S	D	В	_	RM1200DG-66S RM1200HE-66S RM1200DB-66S	D H D	G C B	- -	RM1200DG-90F	D	G	10				
					RM1200DC-66X RM1200DG-66X	D D	C G	11 10								
1500A					RM1500HE-66F RM1500DC-66F	H	CC	-	RM1500DG-90X	D	G	10				
1800A	RM1800HE-34S	Н	С	-												
Connection						Н	Ę		D r							

[Type]

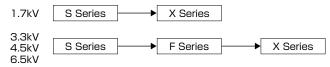
B:Cu base plate 6kV Isolation C:AlSiC base plate 6kV Isolation

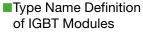
G:AlSiC base plate 10kV Isolation

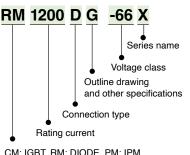
★★: Under development

The outline drawing is written the figure of principal part numbers that have a common dimension. Non-recommended: Please contact to the sales offices.

#### ■ Evolution of HVDIODE Module Series

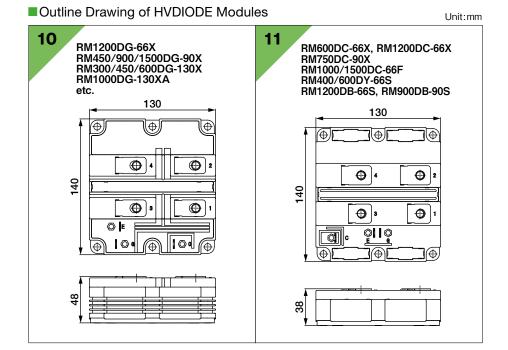






CM: IGBT, RM: DIODE, PM: IPM

### **Lineup of HVDIODE Modules**



### **Lineup of MOSFET Modules**

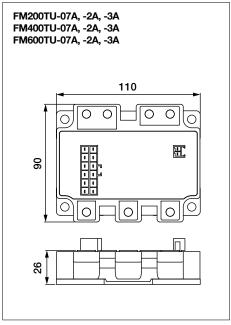
#### ■ Series Matrix of MOSFET Modules

RoHS directive (2011/65/EU, (EU)2015/863) compliant

V <sub>DSS</sub>	75V	ection	100V Conr	nection	150V	Conne	ction
100A	FM200TU-07A	Т	FM200TU-2A	Т	FM200TU-3A		Т
200A	FM400TU-07A	Т	FM400TU-2A	Т	FM400TU-3A		Т
300A	FM600TU-07A	Т	FM600TU-2A	Т	FM600TU-3A		Т
Connection			T				

### ■Outline Drawing of MOSFET Modules

Unit:mm



Data sheet here



### Series, Main Application

	Series	Main Application
Jl	•	xEV

### **Rated Lineup**

		Rated	current
		600A	700A
Rated voltage	650V		
voltage	0301		

\* 700A product has an optional specification with an insert nut embedded in the board mounting boss. Please contact us if necessary.



### **Featured Products**

Package with 6-in-1 connection and integrated water-cooled fin contributes to more compact, high-power

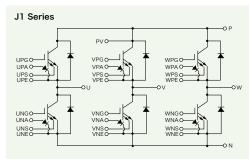
### J1 Series power Modules for xEV

CT600C1A060-A, CT700CJ1A060-A

- <Main Features>
- •Integrated direct water-cooling structure with cooling fins and 6-in-1 connection contribute to more compact inverters for xEV
- ·Direct lead bonding (DLB) structure ensures high reliability
- Loss further reduced by incorporating 7th-generation IGBT built with a CSTBT™\* structure
- On-chip current sensor that enables high-speed current-cutoff protection is installed
- •Completely lead-free, confirms to RoHS directive (2011/65/EU)
- •Suitable for a variety of electric and hybrid vehicle inverters

\*CSTBT: Mitsubishi Electric's unique IGBT that utillizes the carrier cumulative effect.

#### **■ Block Diagram**



### ■ Features

#### Common

- Long power/temperature cycle life
- High-precision on-chip temperrature sensor
- High traceability in managing materials/components for each product throughout the entire production process
- Package structure compliant with the End-of-Life-Vehicles Directive, regulations relating to substances of environmental concern

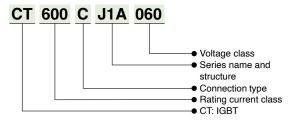
### **Power Modules for xEV**

### ■Matrix of 650V Power Modules

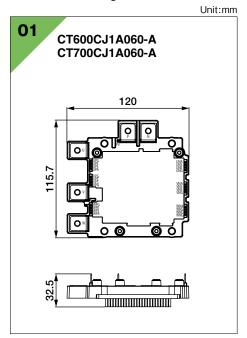
Vces	650V				
Series	J1 Series				
lc \	Power Module with pin fin	Connection	No.		
600A	CT600CJ1A060-A	С	01		
700A	CT700CJ1A060-A	С	01		
Connection	C				

<sup>\* 700</sup>A product has an optional specification with an insert nut embedded in the board mounting boss. Please contact us if necessary.

### ■Type Name Definition of Power Modules for xEV



### ■Outline Drawing of Power Modules for xEV



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